

SONNENSCHEIN, NATH & ROSENTHAL

8000 Sears Tower 233 S. Wacker Drive Chicago, IL 60606 312/876-0200

APPLICANT(S): Masamitsu Ino et al.

ATTORNEY DOCKET NO.: 09792909-4645

SERIAL NO.

09/678,459

GROUP ART UNIT:

1725--

DATE FILED:

October 3, 2000

EXAMINER:

Geoffrey Evans

INVENTION:

"THIN FILM SEMICONDUCTOR DEVICE (As Amended)"

AMENDMENT "B"

Hon. Assistant Commissioner of Patents

Washington D.C. 2023

SIR:

Transmitted herewith is an amendment in the above-identified application.

Additional claim fee is required.

The fee has been calculated as shown below.

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TC 1700

30 1140 00011	calculated as sile		CLAIMS AS AMENDE	D		
	(2) CLAIMS REMAINING AFTER AMENDMENT		(4) HIGHEST NO. PREVIOUSLY PAID FOR	(5) PRESENT EXTRA	(6) RATE	(7) ADDITIONA FEE
TOTAL CLAIMS		MINUS		0	() X 9.00 () X 18.00	0.00
ÍNDEP. CLAIMS		MINUS		0	() X 39.00 (5) X 84.00	0.00
Application amended to contain any multiple dependent claims not previously paid for.			() YES (X) NO	() \$135.00 () \$270.00 ONE_TIME		
TOTAL ADDITIONAL FOR THIS AMENDING				IENT	\$0.00	

_ Applicant petitions the Commissioner of Patents and Trademarks to extend this time for response to the Office Action dated _____ for _ months so that the period for response is extended to _____.

The Commissioner is hereby authorized to charge the extension of time fee of \$____ to deposit account no.

A check in the amount of \$____ is attached to cover the additional claim fee.

The Commissioner is hereby authorized to charge any additional fees which may be required, or to credit any overpayment to account No. 19-3140. A duplicate of this sheet is enclosed.

When phoning re this application, please call 312/876-8000 - Ext. 2606.

SONNENSCHEIN NATH & ROSENTHAL

DATE: December 7, 2002

BY P. P. (Reg. No. 45,034)
Christopher P. Rauch

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited as first class mail in an envelope addressed to Asst. Commissioner of Patents, Washington, D.C. 20231 on <u>December 7, 2002</u>.

Christopher P. Rauch

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Assistant Commissioner of Patents

Washington, D.C. 20231

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SIR:

This Amendment "B" is filed in response to the Office Action of September 1 Please reconsider the application in view of the amendment and remarks presented below.

AMENDMENT "B"

IN THE TITLE OF THE INVENTION

Please replace the Title of the Invention with the following replacement Title of the Invention:

--THIN FILM SEMICONDUCTOR DEVICE--

IN THE ABSTRACT OF THE DISCLOSURE

Please replace the Abstract of the Disclosure with the following replacement Abstract of the Disclosure:

-- A laser annealing apparatus for fabricating a thin film semiconductor device integratedly formed with thin film transistors each of which includes a semiconducting thin film formed on the surface of an insulating substrate spread in longitudinal and lateral directions and then crystallized. A band-shaped pulsed laser beam irradiates the insulating substrate along the longitudinal direction. The laser beam is simultaneously moved in the lateral direction with a specific movement pitch while partially overlapping regions irradiated with the laser beam. The movement pitch of the laser beam is set at a value equal to an arrangement pitch of the thin film transistors or at a value larger by a factor of an integer than the arrangement pitch. The insulating substrate is previously positioned such that the boundaries of the partially overlapped irradiated regions are not overlapped on a channel region of any of the thin film transistors.--

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